

Vishay Semiconductors

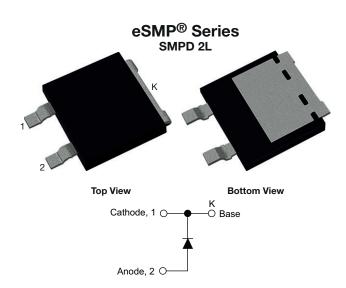
RoHS

COMPLIANT

HALOGEN

FREE

650 V Power SiC Gen 3 Merged PIN Schottky Diode, 12 A



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I _F	12 A			
V _R	650 V			
V _F at I _F at 25 °C, typ.	1.30 V			
T _J max.	175 °C			
I _R at V _R at 175 °C	20 μΑ			
Q _C (V _R = 400 V)	34 nC			
Package	SMPD 2L			
Circuit configuration	Single			

FEATURES

- Creepage and clearance distance 3.6 mm minimum
- Very low profile typical height of 1.7mm
- Majority carrier diode using Schottky technology on SiC wide band gap material
- Improved V_F and efficiency by thin wafer technology
- Positive V_F temperature coefficient for easy paralleling
- · Virtually no recovery tail and no switching losses
- · Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 2 whisker test
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

MECHANICAL DATA

Case: SMPD 2L

Molding compound meets UL 94 V-0 flammability rating

Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

MAXIMUM RATINGS (T _A = 25 °C unless otherwise specified)					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V_{RRM}		650	V	
Continuous forward current	I _F	T _M = 149 °C (DC)	12	Α	
DC blocking voltage	V_{DC}		650	V	
Repetitive peak surge current	I _{FRM}	T_M = 25 °C, f = 50 Hz, square wave, DC = 25 %	61	Α	
Non-repetitive peak forward surge current	I _{FSM}	$T_M = 25$ °C, $t_p = 10$ ms, half sine wave	83	А	
		$T_M = 110$ °C, $t_p = 10$ ms, half sine wave	74		
	P _{tot} (1)	T _M = 25 °C	105	W	
Power dissipation		T _M = 110 °C	45		
rower dissipation	P _{tot} (2)	T _M = 25 °C	136	- W	
		T _M = 110 °C	59		
l ² t value	∫i ² dt	T _M = 25 °C	34.5	A ² s	
i-t value		T _M = 110 °C	27	7 ~5	
Operating junction and storage temperatures	T _J ⁽³⁾ , T _{Stg}		-55 to +175	°C	

Notes

- (1) Based on maximum Rth
- (2) Based on typical Rth
- (3) The heat generated must be less than the thermal conductivity from junction-to-ambient: $dP_D/dT_J < 1/R_{\theta,JA}$



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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
		I _F = 12 A	-	1.3	1.5	
Forward voltage	V _F	I _F = 12 A, T _J = 150 °C	-	1.50	1.85	V
		I _F = 12 A, T _J = 175 °C	-	1.58	-	
Reverse leakage current	I _R	$V_R = V_R$ rated		0.80	65	μА
		V _R = V _R rated, T _J = 150 °C	-	12	150	
		V _R = V _R rated, T _J = 175 °C	-	20	-	
Total capacitance	С	V _R = 1 V, f = 1 MHz		535	-	nE.
		V _R = 400 V, f = 1 MHz	-	54	-	pF
Total capacitive charge	Q _C	V _R = 400 V, f = 1 MHz	-	34	-	nC

THERMAL - MECHANICAL SPECIFICATIONS (T _A = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction-to-mount	R_{thJM}		-	1.1	1.4	°C/W
Marking device				3C12I	ED07T	

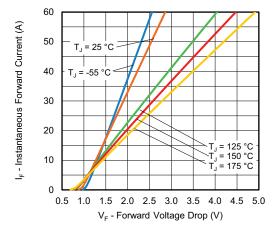


Fig. 1 - Typical Forward Voltage Drop Characteristics

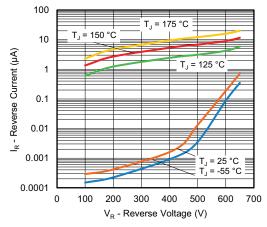


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

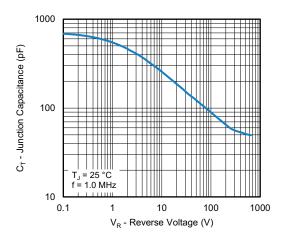


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

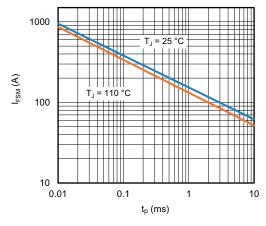


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)



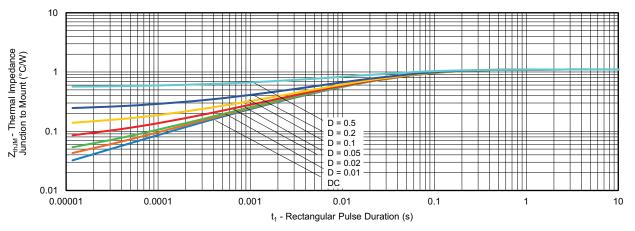


Fig. 5 - Typical Thermal Impedance Z_{thJM} Characteristics

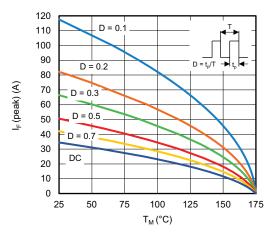


Fig. 6 - Peak Forward Current vs. Maximum Allowable Mount Temperature

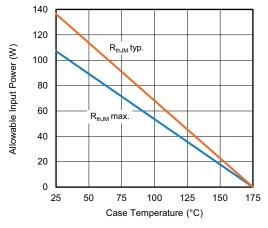


Fig. 7 - Forward Power Loss Characteristics

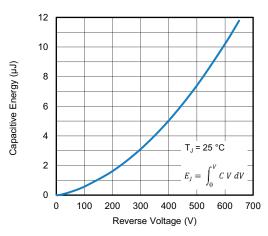


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

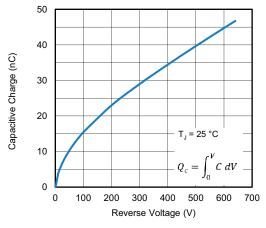


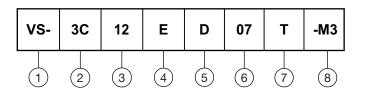
Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage



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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - 3C = SiC diode, Generation 3

Current rating (12 = 12 A)

- E = single diode

5 - Package SMPD 2L

6 - Voltage rating: (07 = 650 V)

7 - T = true 2 pin

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

ORDERING INFO	RMATION			
ORDERING P/N	UNIT WEIGHT	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
VS-3C12ED07T-M3/I	0.52 g	I	2000/reel	13" diameter plastic tape and reel

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?97059			
Part marking information	www.vishay.com/doc?97105			
Packaging information	www.vishay.com/doc?88869			



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